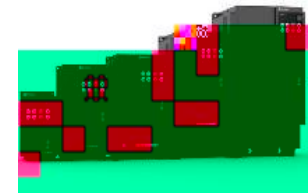


1. G3 1.6um
2. 1200V 100A @ Tc= 100
- 3.
- 4.

Product Name	V _{CES} (V)	I _c (A)	V _{GE(th)} (V)	V _{CE(sat)} (V)	V _F (V)	P _d (W)	T _j
DGQ100N120CTL2A	1200V	100A	5.8	1.5	2.00	883	-40~175

IGBT

To-247PLUS 1200V



Originals

1. 600V breakdown voltage, $I_{Tc} = 100A$
2. 600V breakdown voltage, $I_{Tc} = 100A$
3. Low conduction loss, suitable for low to mid frequency applications
4. Strong short-circuit capacity

Yangjie Technology recently launched a new generation of $600V$ $100A$ SiC MOSFETs

New Product Announcement